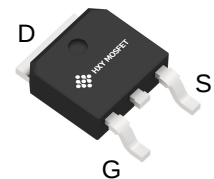




Description

The HXY70P03D uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



TO-252-2L

General Features

$V_{DS} = -30V$ $I_D = -70A$

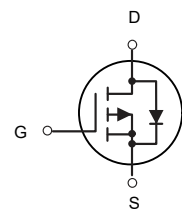
$R_{DS(ON)} < 10m\Omega$ @ $V_{GS} = -10V$

Application

Battery protection

Load switch

Uninterruptible power supply



P-Channel MOSFET

Ordering Information

Product ID	Pack	Brand	Qty(PCS)
HXY70P03D	TO252-2L	HXY MOSFET	2500

Absolute Maximum Ratings (Tc=25°C unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, V_{GS} @ -10V ^{1,6}	-70	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, V_{GS} @ -10V ^{1,6}	-50	A
I_{DM}	Pulsed Drain Current ²	-200	A
EAS	Single Pulse Avalanche Energy ³	80	mJ
I_{AS}	Avalanche Current	-40	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	90	W
T_{STG}	Storage Temperature Range	-55 to 175	°C
T_J	Operating Junction Temperature Range	-55 to 175	°C
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹ ($t \leq 10S$)	20	°C/W
	Thermal Resistance Junction-ambient ¹ (Steady State)	50	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-case ¹	1.6	°C/W



Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

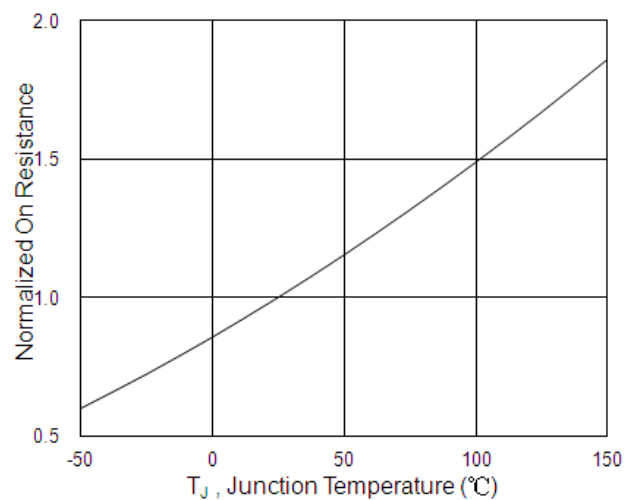
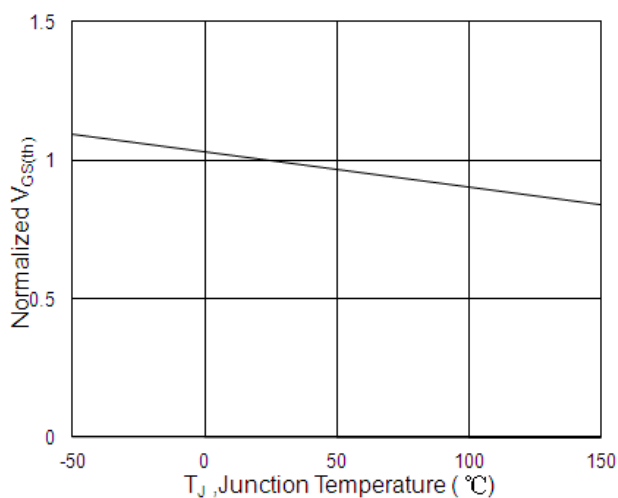
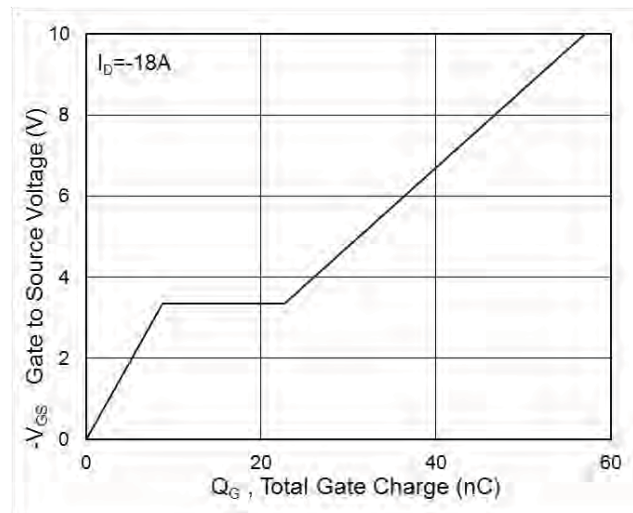
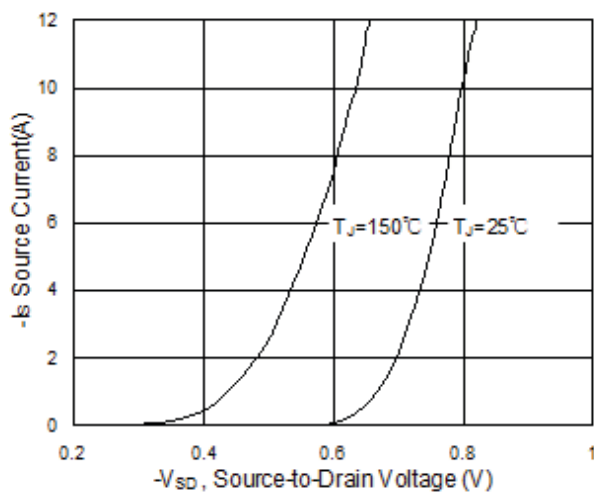
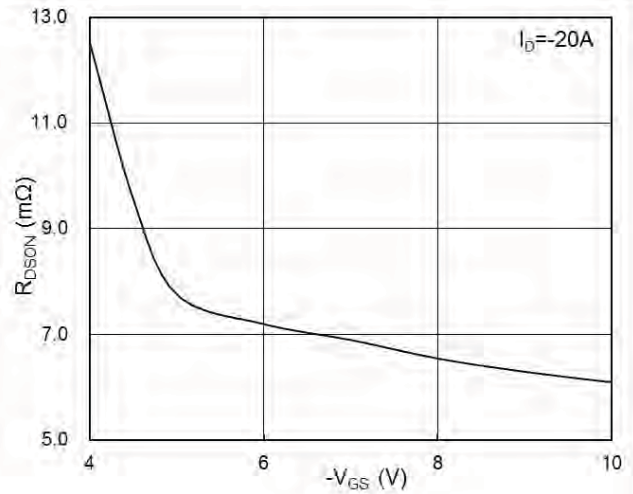
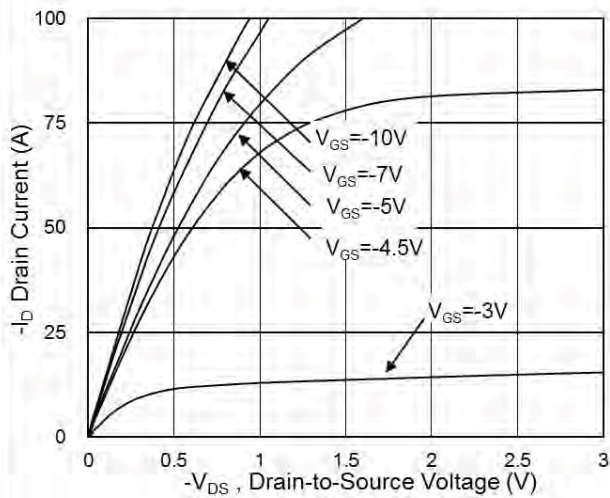
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V$, $I_D=-20A$	---	7	10	$m\Omega$
		$V_{GS}=-4.5V$, $I_D=-15A$	---	11	18	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-1.2	---	-2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-24V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-24V$, $V_{GS}=0V$, $T_J=55^\circ\text{C}$	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	1.2	---	Ω
Q_g	Total Gate Charge (-10V)	$V_{DS}=-15V$, $V_{GS}=-10V$ $I_D=-18A$	---	60	---	nC
Q_{gs}	Gate-Source Charge		---	9	---	
Q_{gd}	Gate-Drain Charge		---	15	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-15V$ $V_{GS}=-10V$ $R_G=3.3\Omega$, $I_D=-20A$	---	17	---	ns
T_r	Rise Time		---	40	---	
$T_{d(off)}$	Turn-Off Delay Time		---	55	---	
T_f	Fall Time		---	13	---	
C_{iss}	Input Capacitance	$V_{DS}=-25V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	3450	---	pF
C_{oss}	Output Capacitance		---	255	---	
C_{rss}	Reverse Transfer Capacitance		---	140	---	
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	-70	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=-1A$, $T_J=25^\circ\text{C}$	---	---	-1.2	V
t_{rr}	Reverse Recovery Time	$I_F=-20A$, $di/dt=100A/\mu s$, $T_J=25^\circ\text{C}$	---	22	---	nS
Q_{rr}	Reverse Recovery Charge		---	72	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=-50V$, $V_{GS}=-10V$, $L=0.1mH$, $I_{AS}=-40A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation
- 6.The maximum current rating is package limited.



Typical Characteristics



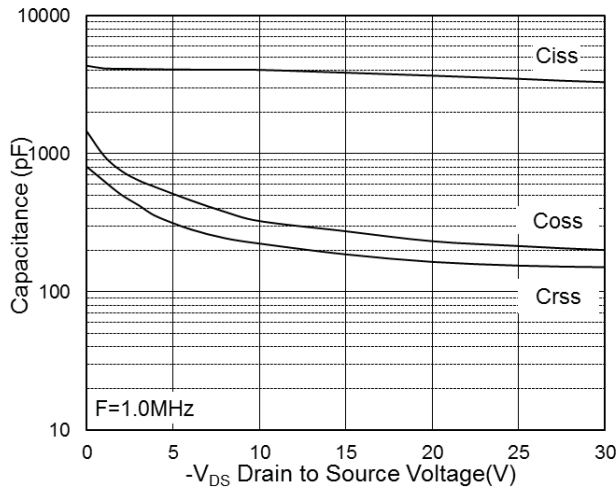


Fig.7 Capacitance

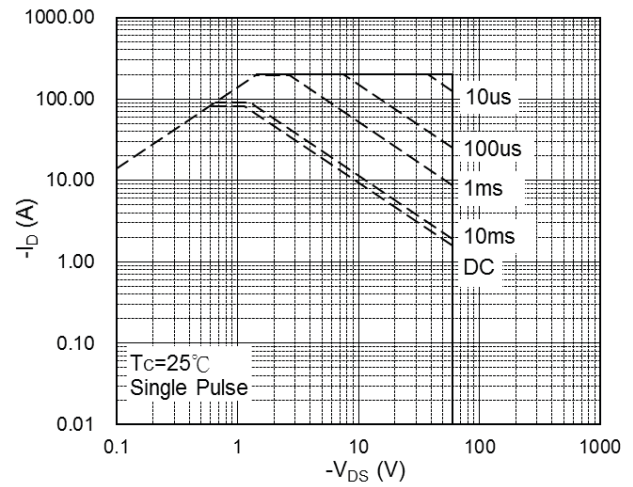


Fig.8 Safe Operating Area

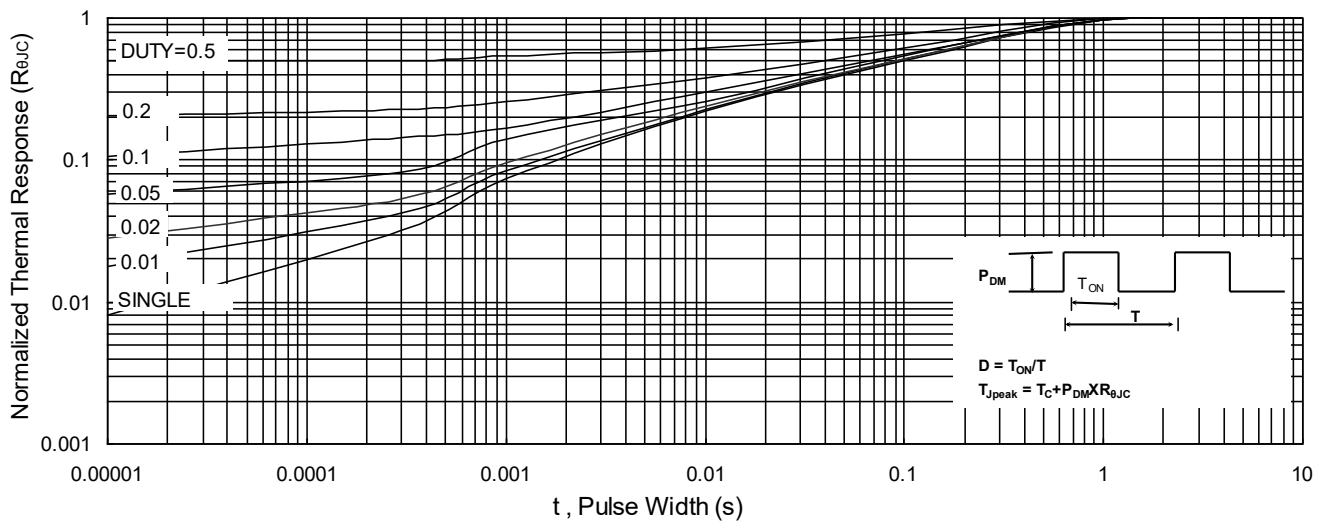


Fig.9 Normalized Maximum Transient Thermal Impedance

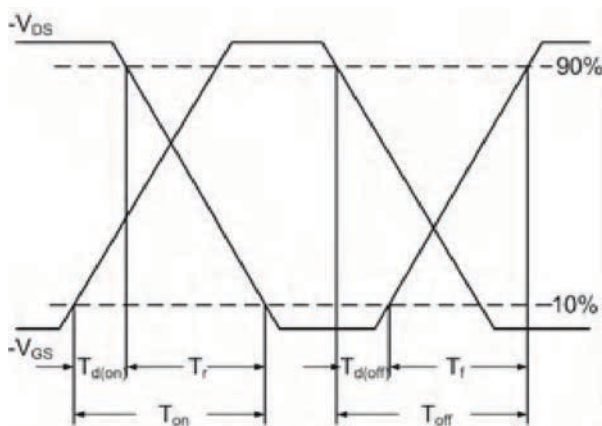


Fig.10 Switching Time Waveform

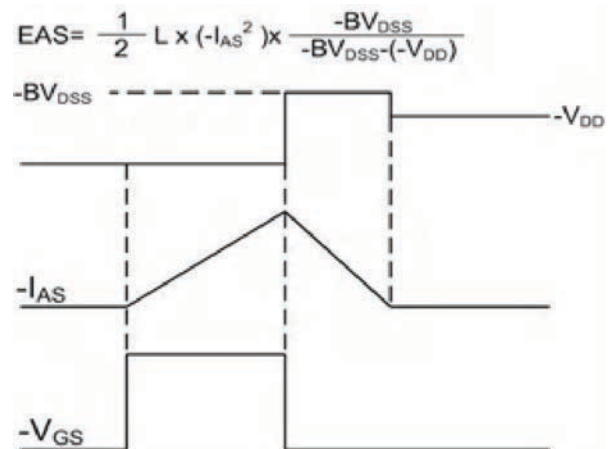
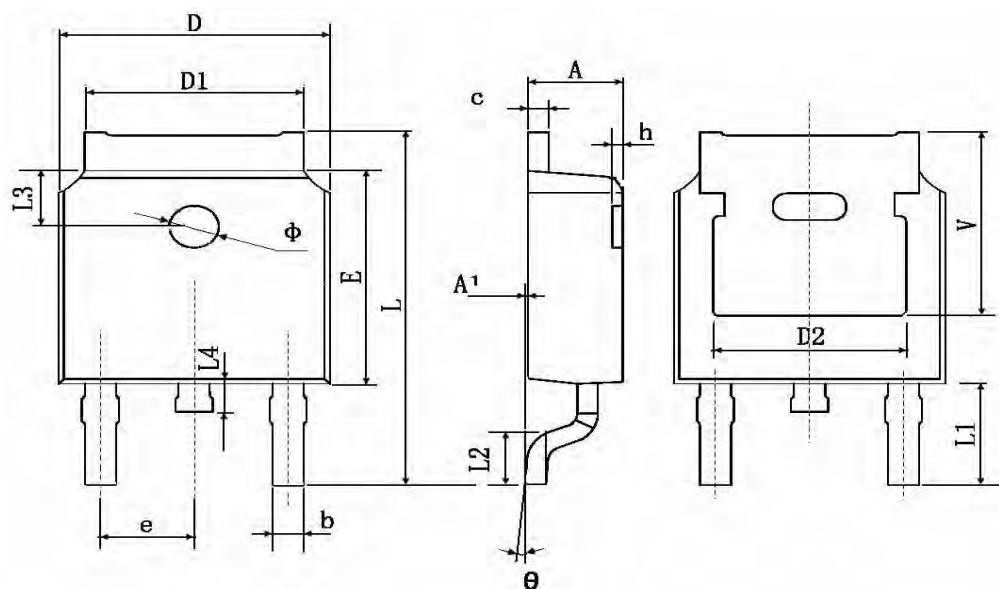


Fig.11 Unclamped Inductive Switching Waveform



TO252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



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